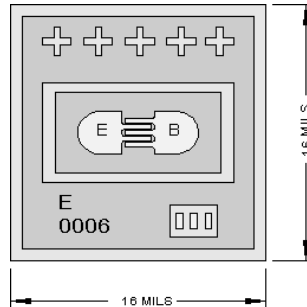


**Chip Type 2C4957**  
**Geometry 0006**  
**Polarity PNP**

**Generic Packaged Parts:**

**2N4957, 2N4958, 2N4959**



[Request Quotation](#)

Chip type **2C4957** by Semicoa Semiconductors provides performance similar to these devices.

**Part Numbers:**

[2N4957](#), [2N4957UB](#), 2N4958, 2N4958UB, 2N4959, 2N4959UB, SD4957, SD4957F, SQ4957, SQ4957F

**Product Summary:**

**APPLICATIONS:**

Designed for high-gain, low-noise class A amplifiers, oscillators and mixers.

**Features: Special Characteristics**

$f_t = 1.6 \text{ GHz (typ) at } 2.0 \text{ mA/10V}$

Radiation graphs available

**Mechanical Specifications**

<b>Metallization</b>	Top	Al - 12 kÅ min.
	Backside	Au - 6.5 kÅ nom.
<b>Bonding Pad Size</b>	Emitter	2.3 mils x 2.3 mils
	Base	2.3 mils x 2.3 mils
<b>Die Thickness</b>	8 mils nominal	
<b>Chip Area</b>	16 mils x 16 mils	
<b>Top Surface</b>	Silox Passivated	

**Electrical Characteristics**

$T_A = 25^\circ\text{C}$

Parameter	Test conditions	Min	Max	Unit
$BV_{CEO}$	$I_C = 1.0 \text{ mA}$	30	---	V dc
$BV_{CBO}$	$I_C = 100 \mu\text{A}$	30	---	V dc
$BV_{EBO}$	$I_E = 100 \mu\text{A}$	3.0	---	V dc
$I_{CBO}$	$V_{CB} = 10 \text{ V dc}$	---	0.1	$\mu\text{A}$
$h_{FE}$	$V_{CE} = 10 \text{ V}, I_C = 2.0 \text{ mA}$	20	150	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*